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# 2SB1530

Silicon PNP Triple Diffused

# HITACHI

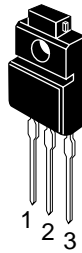
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## Application

Low frequency power amplifier color TV vertical deflection output complementary pair with 2SD2337

## Outline

TO-220FM



1. Base
2. Collector
3. Emitter

## 2SB1530

### Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	$V_{CBO}$	-200	V
Collector to emitter voltage	$V_{CEO}$	-150	V
Emitter to base voltage	$V_{EBO}$	-6	V
Collector current	$I_C$	-2	A
Collector peak current	$I_{C(peak)}$	-5	A
Collector power dissipation	$P_C$	1.5	W
	$P_C^{*1}$	20	
Junction temperature	$T_j$	150	°C
Storage temperature	$T_{stg}$	-45 to +150	°C

Note: 1. Value at  $T_C = 25^\circ\text{C}$ .

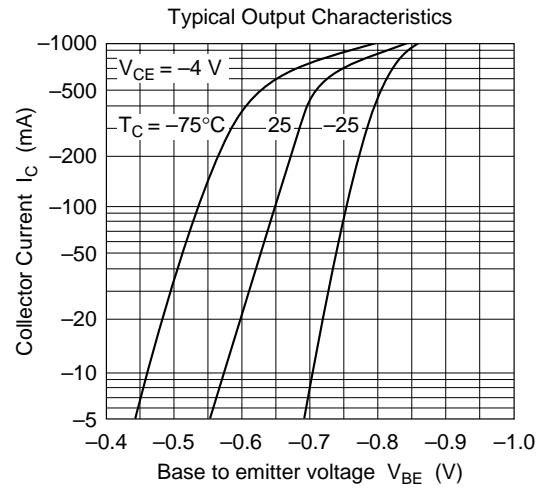
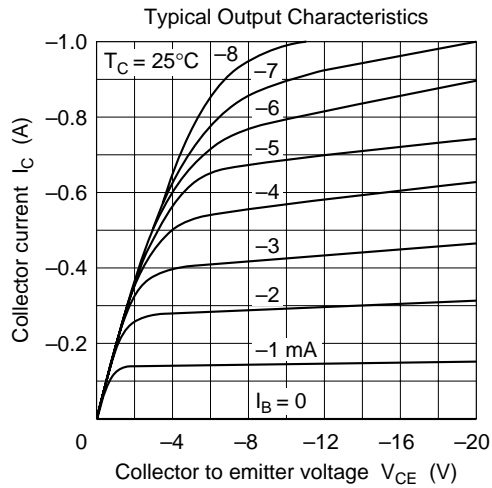
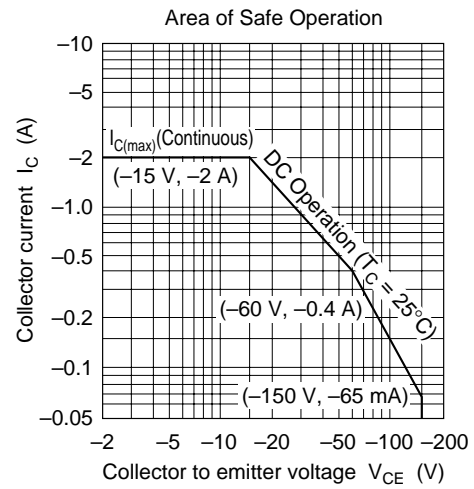
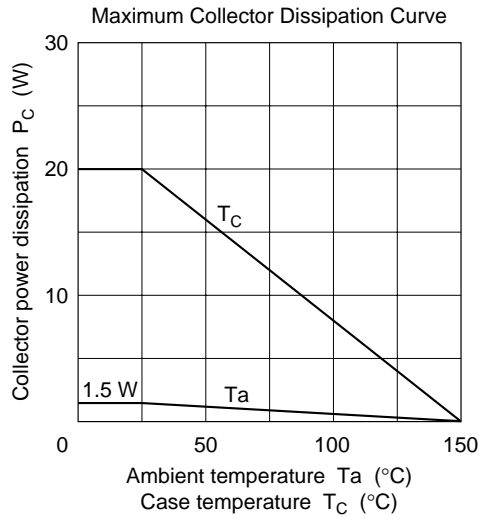
### Electrical Characteristics (Ta = 25°C)

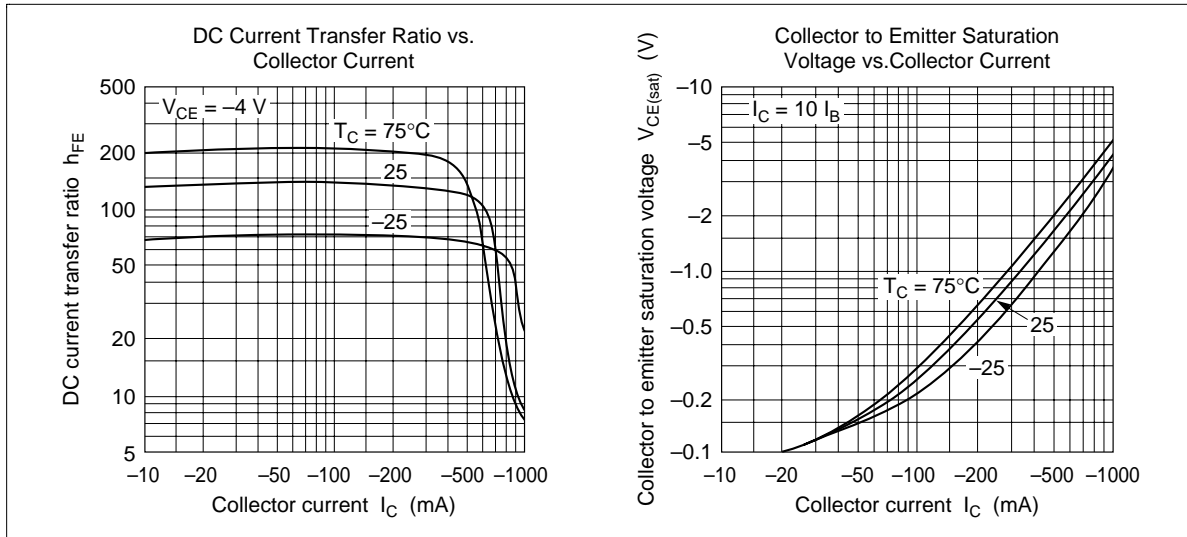
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-150	—	—	V	$I_C = -50\text{ mA}$ , $R_{BE} =$
Emitter to base breakdown voltage	$V_{(BR)EBO}$	-6	—	—	V	$I_E = -5\text{ mA}$ , $I_C = 0$
Collector cutoff current	$I_{CBO}$	—	—	-1	$\mu\text{A}$	$V_{CB} = -120\text{ V}$ , $I_E = 0$
DC current transfer ratio	$h_{FE1}^{*1}$	60	—	200		$V_{CE} = -4\text{ V}$ , $I_C = -50\text{ mA}$
	$h_{FE2}$	60	—	—		$V_{CE} = -10\text{ V}$ , $I_C = -500\text{ mA}^{*2}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	-3	V	$I_C = -500\text{ mA}$ , $I_B = -50\text{ mA}$
Base to emitter voltage	$V_{BE}$	—	—	-1	V	$I_{CE} = -4\text{ A}$ , $I_C = -50\text{ mA}$

Notes: 1. The 2SB1530 is grouped by  $h_{FE1}$  as follows.

B	C
60 to 120	100 to 200

2. Pulse test.





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